

ZXTN2011Z

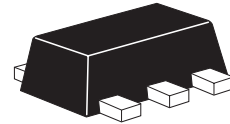
100V NPN LOW SATURATION MEDIUM POWER TRANSISTOR IN SOT89

SUMMARY

$BV_{CEO} = 100V$; $R_{SAT} = 31m\Omega$; $I_C = 4.5A$

DESCRIPTION

Packaged in the SOT89 outline this new low saturation 100V NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.



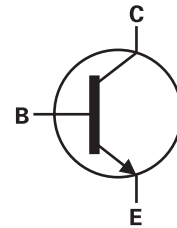
SOT89

FEATURES

- 4.5 amps continuous current
- Up to 10 amps peak current
- Very low saturation voltages

APPLICATIONS

- Motor driving
- Line switching
- High side switches
- Subscriber line interface cards (SLIC)



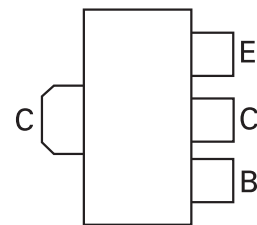
ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXTN2011ZTA	7"	12mm embossed	1,000 units

DEVICE MARKING

853

PINOUT



VIEW

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector base voltage	BV_{CBO}	200	V
Collector emitter voltage	BV_{CEO}	100	V
Emitter base voltage	BV_{EBO}	7	V
Continuous collector current ^(a)	I_C	4.5	A
Peak pulse current	I_{CM}	10	A
Power dissipation at $T_A=25^\circ\text{C}$ ^(a)	P_D	1.5	W
Linear derating factor		12	mW/°C
Power dissipation at $T_A=25^\circ\text{C}$ ^(b)	P_D	2.1	W
Linear derating factor		16.8	mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to ambient ^(a)	$R_{\theta JA}$	83	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	60	°C/W

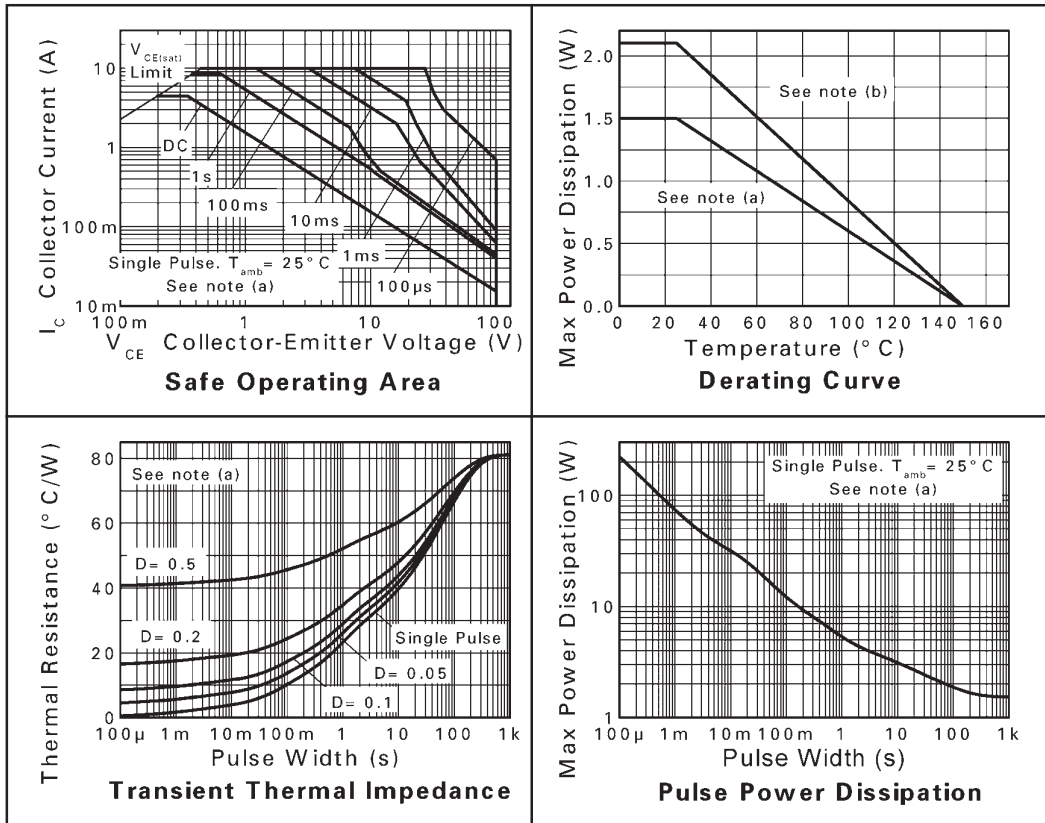
NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

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CHARACTERISTICS



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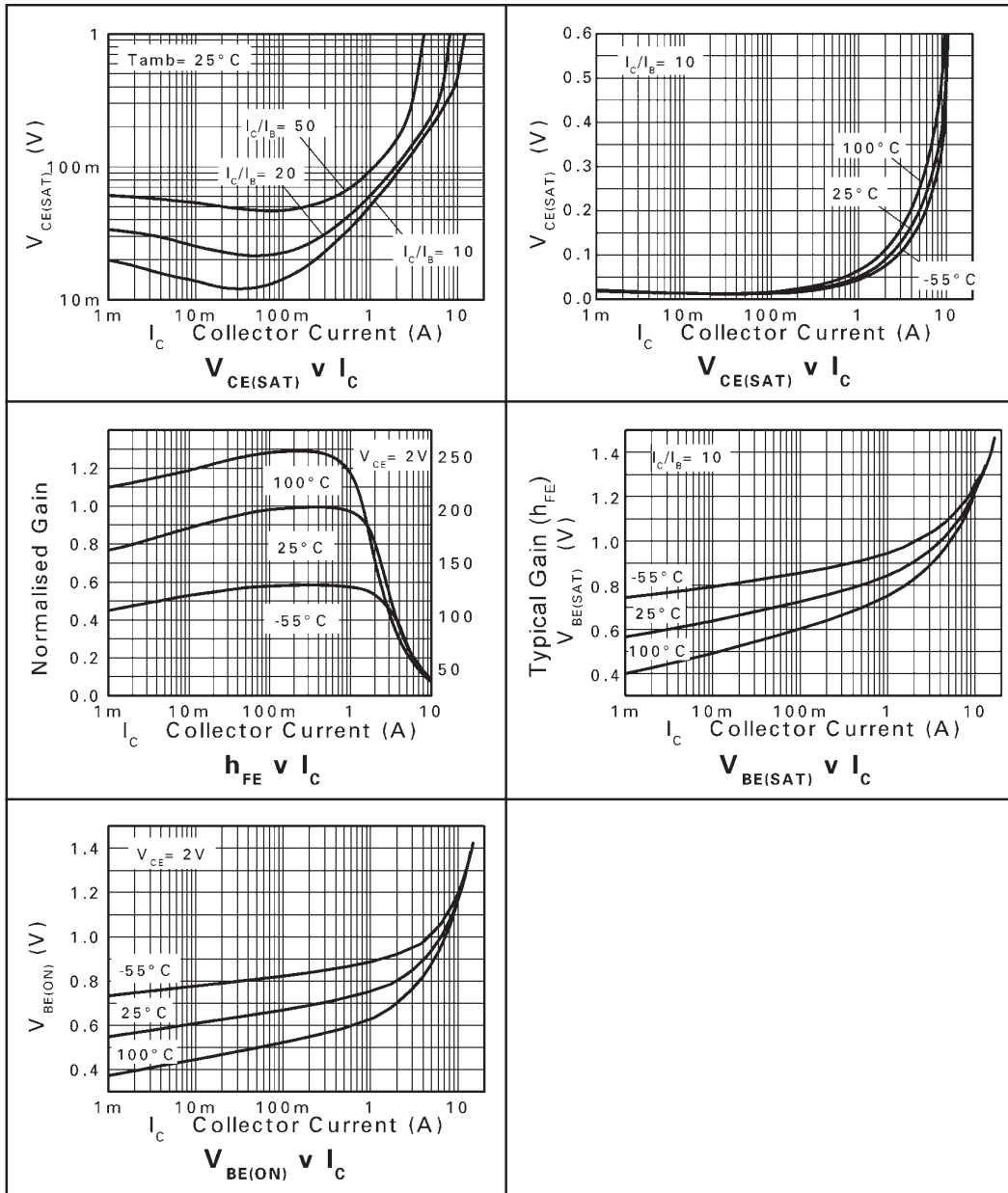
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector base breakdown voltage	BV_{CBO}	200	235		V	$I_C = 100\mu\text{A}$
Collector emitter breakdown voltage	BV_{CER}	200	235		V	$I_C = 1\mu\text{A}$, $R_B \leq 1\text{k}\Omega$
Collector emitter breakdown voltage	BV_{CEO}	100	115		V	$I_C = 10\text{mA}^*$
Emitter base breakdown voltage	BV_{EBO}	7	8.1		V	$I_E = 100\mu\text{A}$
Collector cut-off current	I_{CBO}			50 0.5	nA μA	$V_{CB} = 150\text{V}$ $V_{CB} = 150\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Collector cut-off current	I_{CER} $R \leq 1\text{k}\Omega$			100 0.5	nA μA	$V_{CB} = 150\text{V}$ $V_{CB} = 150\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Emitter cut-off current	I_{EBO}			10	nA	$V_{EB} = 6\text{V}$
Collector-emitter saturation voltage	$V_{CE(SAT)}$		20 45 85 155	30 60 115 195	mV	$I_C = 0.1\text{A}$, $I_B = 5\text{mA}^*$ $I_C = 1\text{A}$, $I_B = 100\text{mA}^*$ $I_C = 2\text{A}$, $I_B = 100\text{mA}^*$ $I_C = 5\text{A}$, $I_B = 500\text{mA}^*$
Base emitter saturation voltage	$V_{BE(SAT)}$		1000	1100	mV	$I_C = 5\text{A}$, $I_B = 500\text{mA}^*$
Base emitter turn on voltage	$V_{BE(ON)}$		900	1000	mV	$I_C = 5\text{A}$, $V_{CE} = 2\text{V}^*$
Static forward current transfer ratio	h_{FE}	100 100 30 10	230 200 60 20	300		$I_C = 10\text{mA}$, $V_{CE} = 2\text{V}^*$ $I_C = 2\text{A}$, $V_{CE} = 2\text{V}^*$ $I_C = 5\text{A}$, $V_{CE} = 2\text{V}^*$ $I_C = 10\text{A}$, $V_{CE} = 2\text{V}^*$
Transition frequency	f_T		130		MHz	$I_C = 100\text{mA}$, $V_{CE} = 10\text{V}$ $f = 50\text{MHz}$
Output capacitance	C_{OBO}		26		pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}^*$
Switching times	t_{ON} t_{OFF}		41 1010		ns	$I_C = 1\text{A}$, $V_{CC} = 10\text{V}$, $I_{B1} = I_{B2} = 100\text{mA}$

* Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

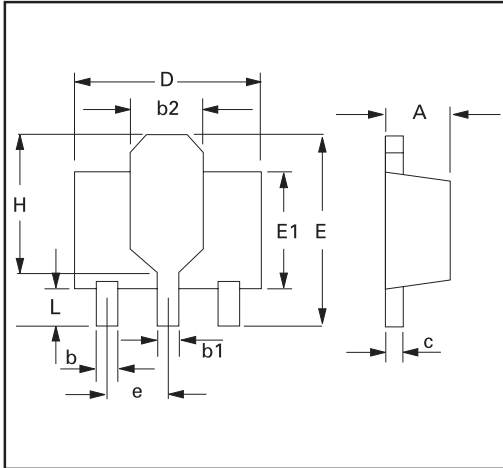
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TYPICAL CHARACTERISTICS



ZXTN2011Z

PACKAGE OUTLINE



PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	e	1.40	1.50	0.055	0.059
b	0.38	0.48	0.015	0.019	E	3.75	4.25	0.150	0.167
b1	-	0.53	-	0.021	E1	-	2.60	-	0.102
b2	1.50	1.80	0.060	0.071	G	2.90	3.00	0.114	0.118
c	0.28	0.44	0.011	0.017	H	2.60	2.85	0.102	0.112
D	4.40	4.60	0.173	0.181	-	-	-	-	-

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park Chadderton, Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europa.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

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ISSUE 2 - MAY 2006